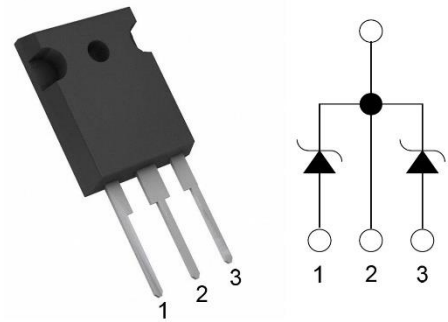


Product Summary

$V_R = 650\text{ V}$
 $I_F = 40\text{ A (}T_C=150^\circ\text{C)}^{**}$
 $Q_C = 88\text{ nC (}V_R=400\text{ V)}^{**}$



TO-247-3

Features

- Zero Forward/Reverse Recovery Current
- High Blocking Voltage
- High Frequency Operation
- Positive Temperature Coefficient on V_F
- Temperature Independent Switching Behavior
- High surge current capability

Benefits

- Higher System Efficiency
- Parallel Device Convenience without thermal runaway
- Higher Temperature Application
- No Switching loss
- Hard Switching & Higher Reliability
- Environmental Protection

Applications

- Servo Drives
- Solar Inverters
- AC/DC converters
- DC/DC converters
- Uninterruptable power supplies

Maximum Ratings ($T_C=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Value	Unit
Peak Repetitive Reverse Voltage	V_{RRM}		650	V
Peak Reverse Surge Voltage	V_{RSM}		650	V
DC Blocking Voltage	V_R		650	V
Continuous Forward Current (per leg / per device)	I_F	$T_C=25^\circ\text{C}$ $T_C=135^\circ\text{C}$ $T_C=145^\circ\text{C}$	46/92 23/46 20/40	A
Non repetitive Forward Surge Current *	I_{FSM}	$T_C = 25^\circ\text{C}$, $t_p=10\text{ ms}$, Half Sine Pulse $T_C = 110^\circ\text{C}$, $t_p=10\text{ ms}$, Half Sine Pulse	120 110	A
Repetitive peak Forward Surge Current *	I_{FRM}	$T_C = 25^\circ\text{C}$, $t_p=10\text{ ms}$, Freq = 0.1Hz, 100 cycles, Half Sine Pulse $T_C = 110^\circ\text{C}$, $t_p=10\text{ ms}$, Freq = 0.1Hz, 100 cycles, Half Sine Pulse	110 100	A
Total power dissipation (per leg / per device)	P_D	$T_C=25^\circ\text{C}$	150/300	W
Operating Junction Temperature	T_J		-55 to 175	$^\circ\text{C}$
Storage Temperature	T_{STG}		-55 to 175	$^\circ\text{C}$

Note : * Per leg ** Per device

Electrical Characteristics

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
DC Blocking Voltage *	V_{DC}	$T_J = 25^\circ C$	650			V
Forward Voltage *	V_F	$I_F = 20A, T_J = 25^\circ C$		1.5	1.8	V
		$I_F = 20A, T_J = 125^\circ C$		1.6		V
		$I_F = 20A, T_J = 175^\circ C$		1.7		V
Reverse Current *	I_R	$V_R = 650V, T_J = 25^\circ C$		20	80	μA
		$V_R = 650V, T_J = 125^\circ C$		120		μA
		$V_R = 650V, T_J = 175^\circ C$		250		μA
Total Capacitive Charge *	Q_C	$V_R = 400V, T_J = 25^\circ C$		44		nC
Total Capacitance *	C	$V_R = 1V, T_J = 25^\circ C,$ Freq = 1MHz		770		pF
		$V_R = 200V, T_J = 25^\circ C,$ Freq = 1MHz		90		
		$V_R = 400V, T_J = 25^\circ C,$ Freq = 1MHz		64		

Note: This is a majority carrier diode, so there is no reverse recovery charge

Thermal Characteristics

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Thermal Resistance (per device)	$R_{th(j-c)}$	junction-case		0.5		$^\circ C/W$

Note : * Per leg ** Per device

Typical Electrical Curves (Per Leg)

Figure 1. Forward Characteristics

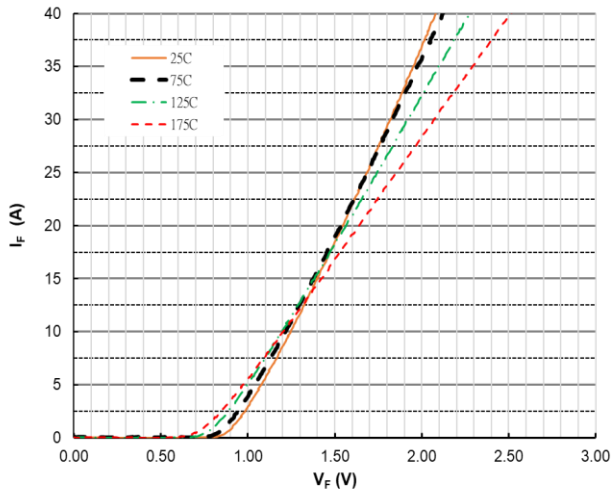


Figure 2. Forward Characteristics

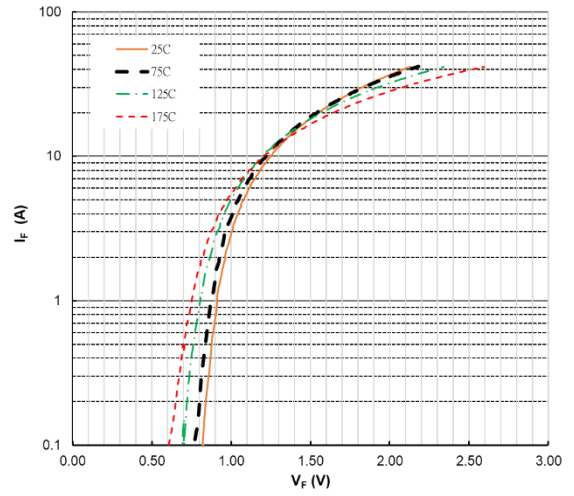


Figure 3. Reverse Characteristics

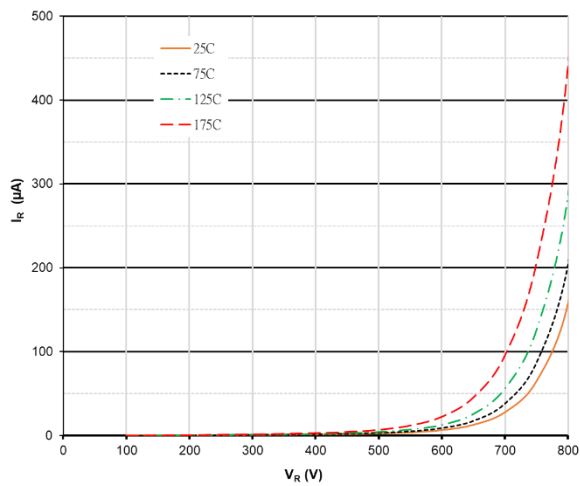


Figure 4. Power Derating

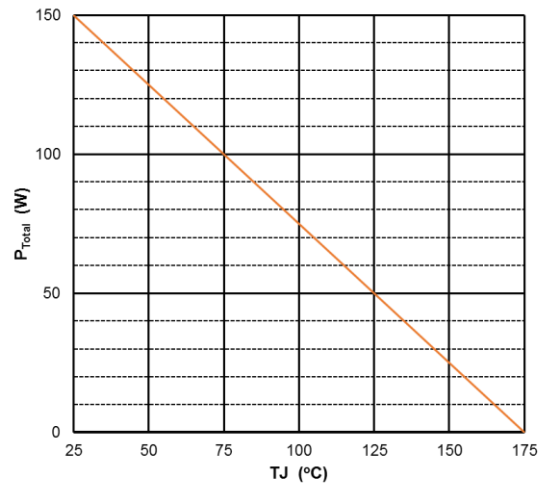


Figure 5. Capacitance vs Reverse Voltage

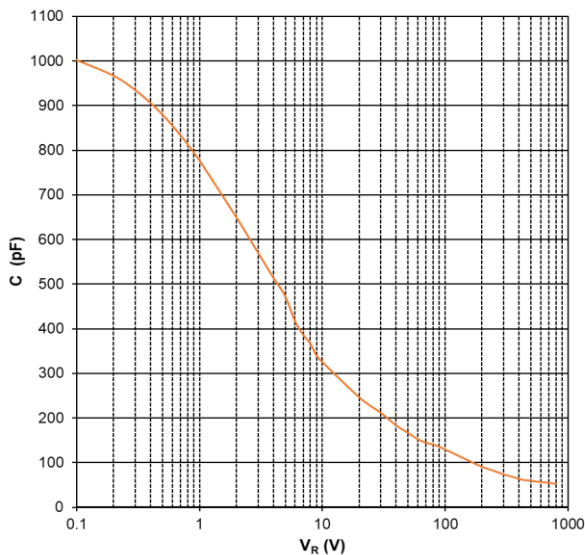
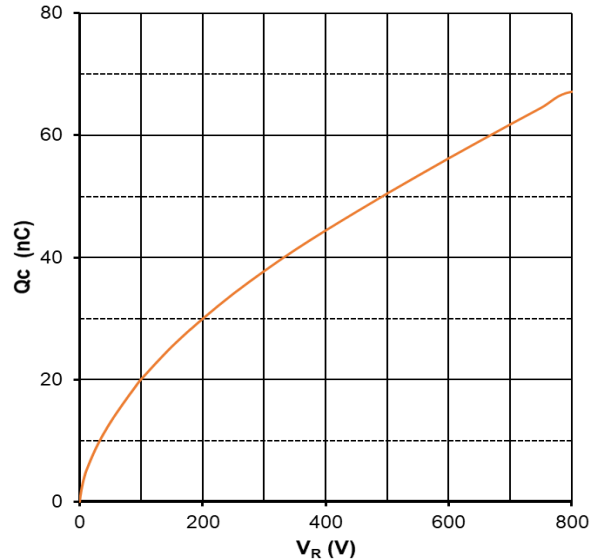
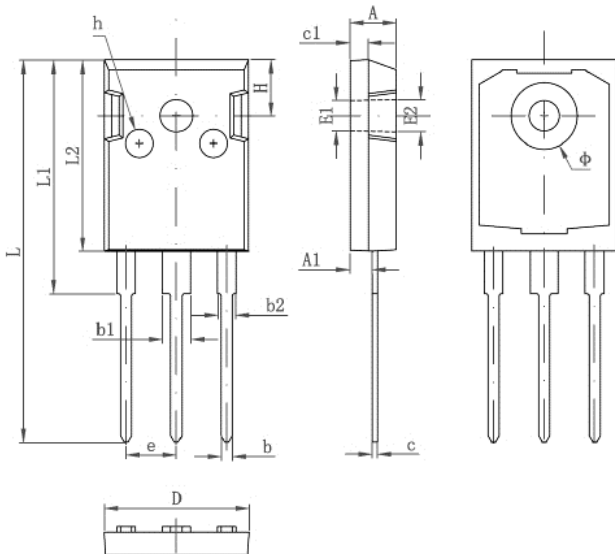


Figure 6. Recovery Charge vs Reverse Voltage



Package Dimensions

(TO-247-3 Package)



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	4.850	5.150	0.191	0.200
A1	2.200	2.600	0.087	0.102
b	1.000	1.400	0.039	0.055
b1	2.800	3.200	0.110	0.126
b2	1.800	2.200	0.071	0.087
c	0.500	0.700	0.020	0.028
c1	1.900	2.100	0.075	0.083
D	15.450	15.750	0.608	0.620
E1	3.500 REF		0.138 REF	
E2	3.600 REF		0.142 REF	
L	40.900	41.300	1.610	1.626
L1	24.800	25.100	0.976	0.988
L2	20.300	20.600	0.799	0.811
Φ	7.100	7.300	0.280	0.287
e	5.450 TYP		0.215 TYP	
H	5.980 REF		0.235 REF	
h	0.000	0.300	0.000	0.012